



ON Semiconductor®

FGH75T65UPD

650V, 75A Field Stop Trench IGBT

Features

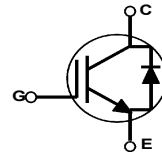
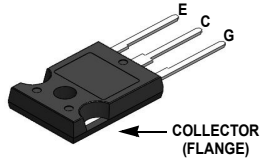
- Maximum Junction Temperature : $T_J = 175^\circ\text{C}$
- Positive Temperature Co-efficient for Easy Parallel Operating
- High Current Capability
- Low Saturation Voltage: $V_{CE(sat)} = 1.65\text{ V(Typ.) @ } I_C = 75\text{ A}$
- 100% of Parts Tested $I_{LM(2)}$
- High Input Impedance
- Tightened Parameter Distribution
- RoHS Compliant
- Short Circuit Ruggedness $> 5\text{ us @ } 25^\circ\text{C}$

General Description

Using innovative field stop trench IGBT technology, ON Semiconductor's new series of field-stop trench IGBTs offer optimum performance for solar inverter, UPS, welder, and digital power generator where low conduction and switching losses are essential.

Applications

- Solar Inverter, UPS, Digital Power Generator



Absolute Maximum Ratings

Symbol	Description	Ratings	Unit
V_{CES}	Collector to Emitter Voltage	650	V
V_{GES}	Gate to Emitter Voltage	± 20	V
	Transient Gate-to-Emitter Voltage	± 25	V
I_C	Collector Current @ $T_C = 25^\circ\text{C}$	150	A
	Collector Current @ $T_C = 100^\circ\text{C}$	75	A
$I_{CM(1)}$	Pulsed Collector Current	225	A
$I_{LM(2)}$	Clamped Inductive Load Current @ $T_C = 25^\circ\text{C}$	225	A
I_F	Diode Forward Current @ $T_C = 25^\circ\text{C}$	75	A
	Diode Forward Current @ $T_C = 100^\circ\text{C}$	50	A
$I_{FM(1)}$	Pulsed Diode Maximum Forward Current	225	A
P_D	Maximum Power Dissipation @ $T_C = 25^\circ\text{C}$	375	W
	Maximum Power Dissipation @ $T_C = 100^\circ\text{C}$	187	W
SCWT	Short Circuit Withstand Time @ $T_C = 25^\circ\text{C}$	5	us
T_J	Operating Junction Temperature	-55 to +175	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55 to +175	$^\circ\text{C}$
T_L	Maximum Lead Temp. for soldering Purposes, 1/8" from case for 5 seconds	300	$^\circ\text{C}$

Notes:

- 1: Repetitive rating: Pulse width limited by max. junction temperature
- 2: $I_C = 225\text{ A}$, $V_{ce} = 400\text{ V}$, $R_g = 10\ \Omega$

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JC}(\text{IGBT})$	Thermal Resistance, Junction to Case	-	0.40	$^\circ\text{C/W}$
$R_{\theta JC}(\text{Diode})$	Thermal Resistance, Junction to Case	-	0.86	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	-	40	$^\circ\text{C/W}$

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FGH75T65UPD	FGH75T65UPD	TO-247 A03	Tube	N/A	N/A	30

Electrical Characteristics of the IGBT T_C = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
Off Characteristics						
BV_{CES}	Collector to Emitter Breakdown Voltage	$V_{GE} = 0\text{ V}, I_C = 1\text{ mA}$	650	-	-	V
$\frac{\Delta BV_{CES}}{\Delta T_J}$	Temperature Coefficient of Breakdown Voltage	$V_{GE} = 0\text{ V}, I_C = 250\text{ }\mu\text{A}$	-	0.65	-	V/°C
I_{CES}	Collector Cut-Off Current	$V_{CE} = V_{CES}, V_{GE} = 0\text{ V}$	-	-	250	μA
I_{GES}	G-E Leakage Current	$V_{GE} = V_{GES}, V_{CE} = 0\text{ V}$	-	-	±400	nA
On Characteristics						
$V_{GE(th)}$	G-E Threshold Voltage	$I_C = 75\text{ mA}, V_{CE} = V_{GE}$	4.0	6.0	7.5	V
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	$I_C = 75\text{ A}, V_{GE} = 15\text{ V}$	-	1.65	2.3	V
		$I_C = 75\text{ A}, V_{GE} = 15\text{ V}, T_C = 175^\circ\text{C}$	-	2.05	-	V
Dynamic Characteristics						
C_{ies}	Input Capacitance	$V_{CE} = 30\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$	-	5665	-	pF
C_{oes}	Output Capacitance		-	205	-	pF
C_{res}	Reverse Transfer Capacitance		-	100	-	pF
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	$V_{CC} = 400\text{ V}, I_C = 75\text{ A}, R_G = 3\text{ }\Omega, V_{GE} = 15\text{ V}, \text{Inductive Load}, T_C = 25^\circ\text{C}$	-	32	42	ns
t_r	Rise Time		-	43	56	ns
$t_{d(off)}$	Turn-Off Delay Time		-	166	216	ns
t_f	Fall Time		-	24	33	ns
E_{on}	Turn-On Switching Loss		-	2.85	3.68	mJ
E_{off}	Turn-Off Switching Loss		-	1.20	1.60	mJ
E_{ts}	Total Switching Loss		-	4.05	5.3	mJ
$t_{d(on)}$	Turn-On Delay Time	$V_{CC} = 400\text{ V}, I_C = 75\text{ A}, R_G = 3\text{ }\Omega, V_{GE} = 15\text{ V}, \text{Inductive Load}, T_C = 175^\circ\text{C}$	-	30	-	ns
t_r	Rise Time		-	57	-	ns
$t_{d(off)}$	Turn-Off Delay Time		-	176	-	ns
t_f	Fall Time		-	21	-	ns
E_{on}	Turn-On Switching Loss		-	4.45	-	mJ
E_{off}	Turn-Off Switching Loss		-	1.60	-	mJ
E_{ts}	Total Switching Loss		-	6.05	-	mJ
T_{sc}	Short Circuit Withstand Time	$V_{GE} = 15\text{ V}, V_{CC} \leq 400\text{ V}, R_g = 10\text{ }\Omega$	5	-	-	us
Q_g	Total Gate Charge	$V_{CE} = 400\text{ V}, I_C = 75\text{ A}, V_{GE} = 15\text{ V}$	-	385	578	nC
Q_{ge}	Gate to Emitter Charge		-	45	68	nC
Q_{gc}	Gate to Collector Charge		-	210	315	nC

Electrical Characteristics of the Diode T_C = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max	Units	
V _{FM}	Diode Forward Voltage	I _F = 50 A	T _C = 25°C	-	2.1	2.6	V
			T _C = 175°C	-	1.7	-	
E _{rec}	Reverse Recovery Energy	I _F = 50 A, di _F /dt = 200 A/μs	T _C = 175°C	-	40	-	μJ
t _{rr}	Diode Reverse Recovery Time		T _C = 25°C	-	65	85	ns
			T _C = 175°C	-	127	-	
Q _{rr}	Diode Reverse Recovery Charge		T _C = 25°C	-	120	170	nC
		T _C = 175°C	-	550	-		

Typical Performance Characteristics

Figure 1. Typical Output Characteristics

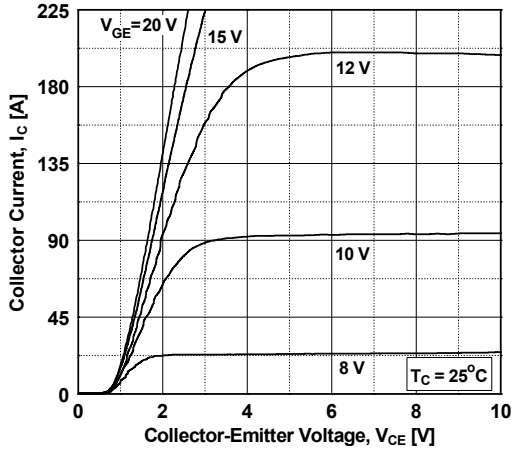


Figure 2. Typical Output Characteristics

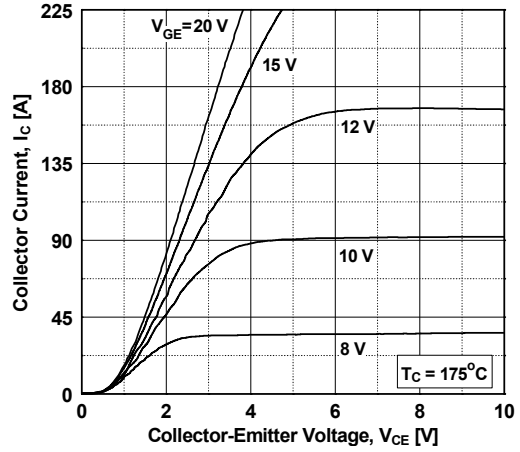


Figure 3. Typical Saturation Voltage Characteristics

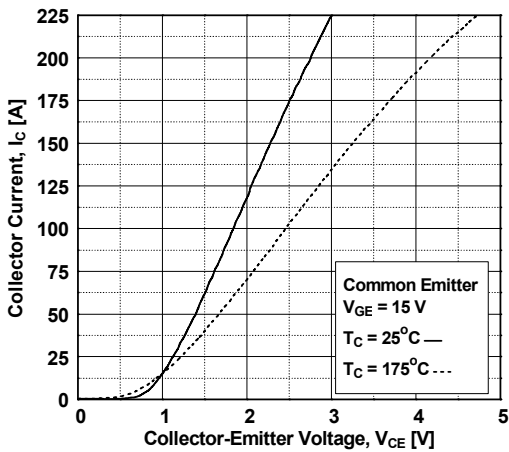


Figure 4. Saturation Voltage vs. Case Temperature at Variant Current Level

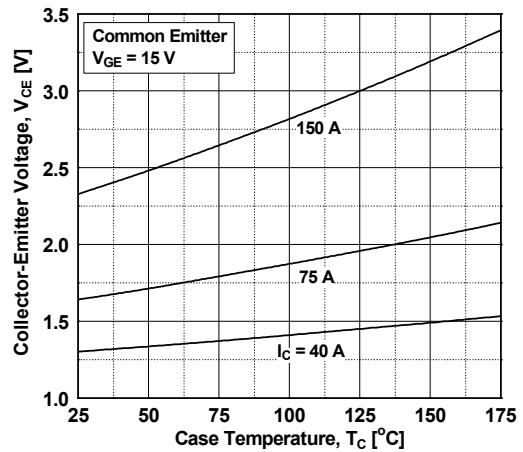


Figure 5. Saturation Voltage vs. V_{GE}

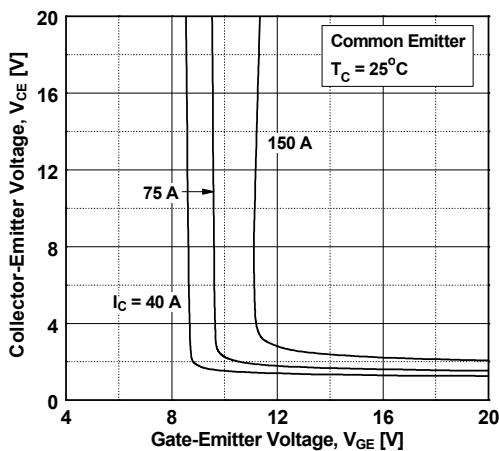
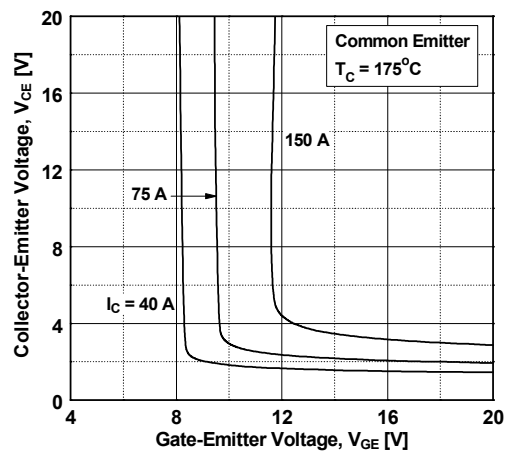


Figure 6. Saturation Voltage vs. V_{GE}



Typical Performance Characteristics

Figure 7. Capacitance Characteristics

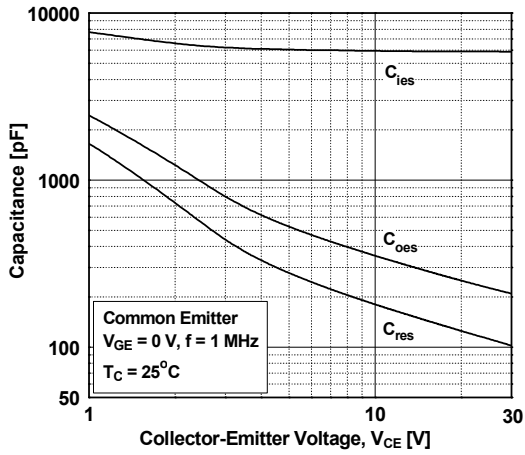


Figure 8. Gate charge Characteristics

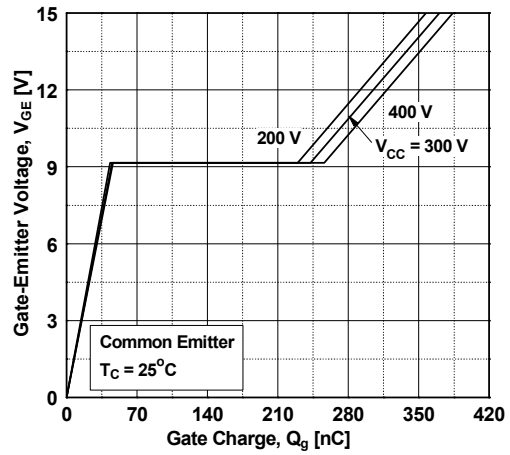


Figure 9. Turn-on Characteristics vs. Gate Resistance

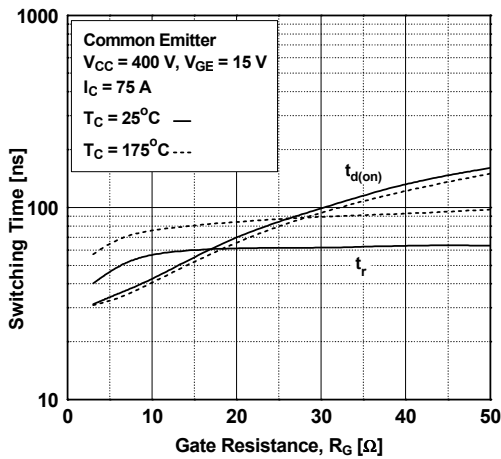


Figure 10. Turn-off Characteristics vs. Gate Resistance

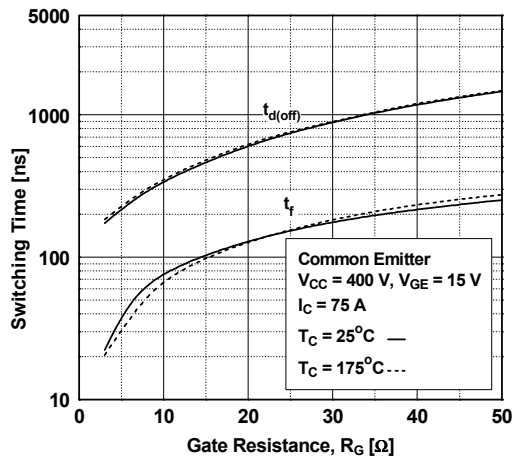


Figure 11. Switching Loss vs. Gate Resistance

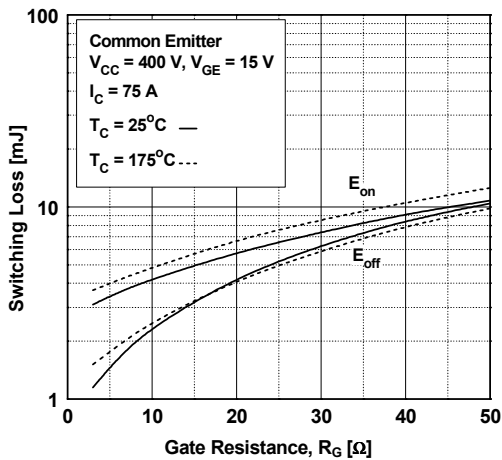
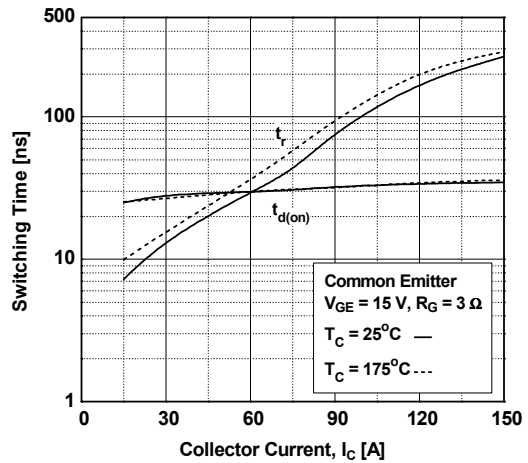


Figure 12. Turn-on Characteristics vs. Collector Current



Typical Performance Characteristics

Figure 13. Turn-off Characteristics vs. Collector Current

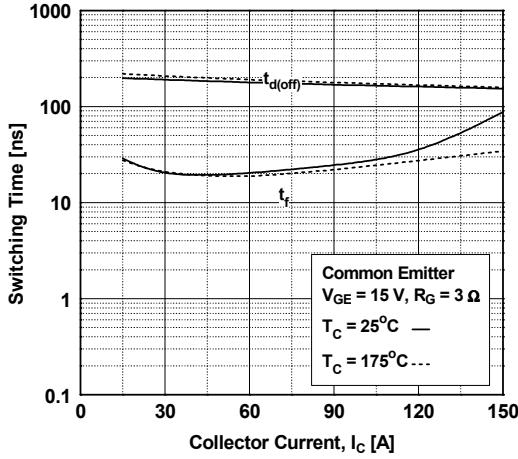


Figure 14. Switching Loss vs. Collector Current

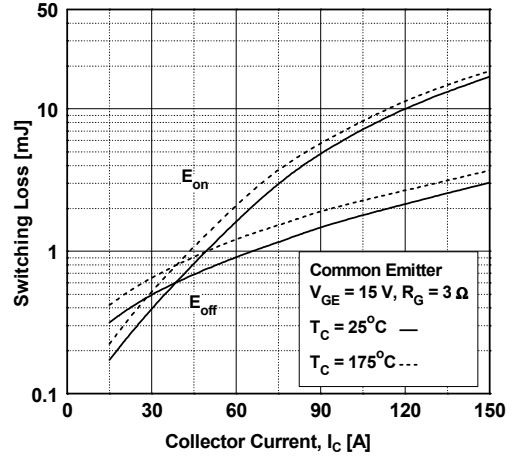


Figure 15. Load Current vs. Frequency

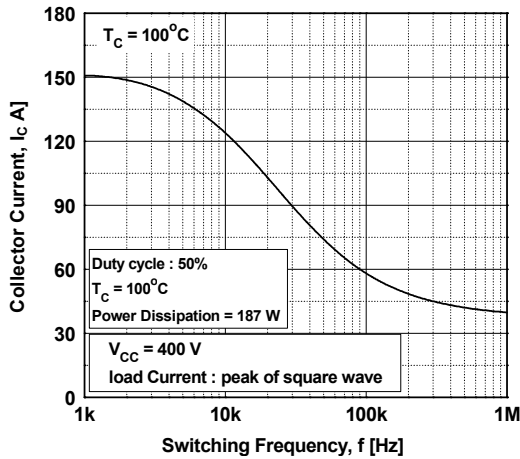


Figure 16. SOA Characteristics

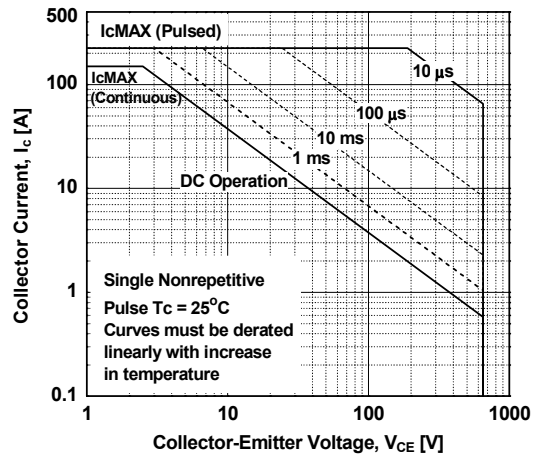


Figure 17. Forward Characteristics

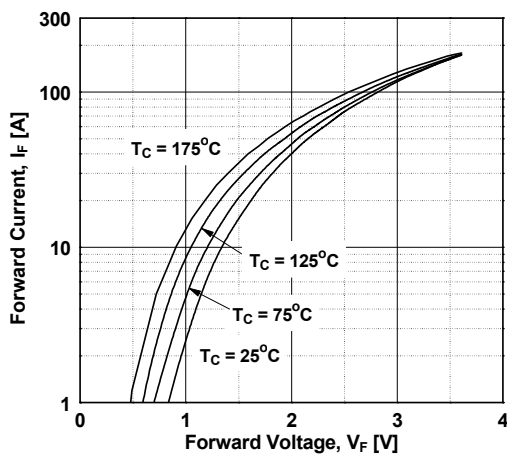
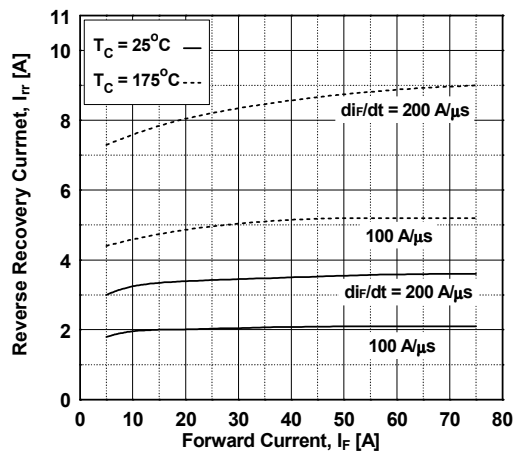


Figure 18. Reverse Recovery Current



Typical Performance Characteristics

Figure 19. Reverse Recovery Time

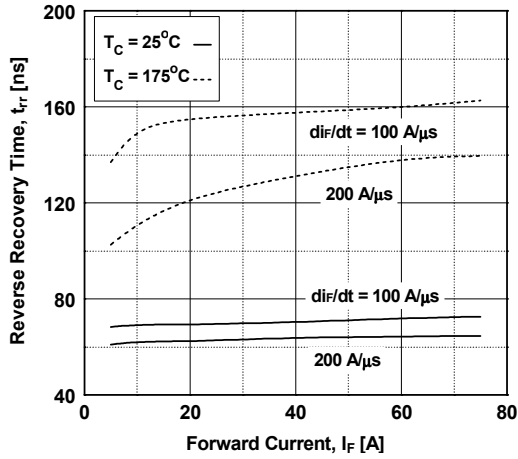


Figure 20. Stored Charge

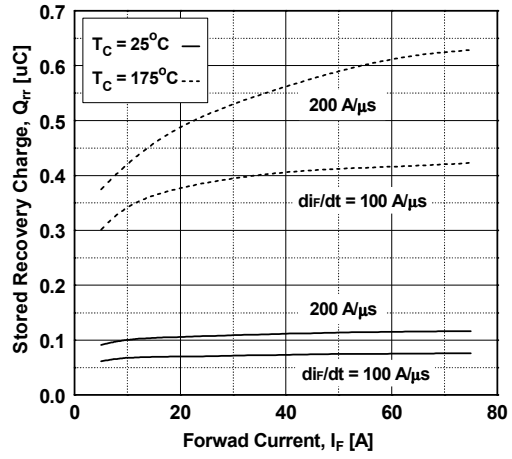


Figure 21. Transient Thermal Impedance of IGBT

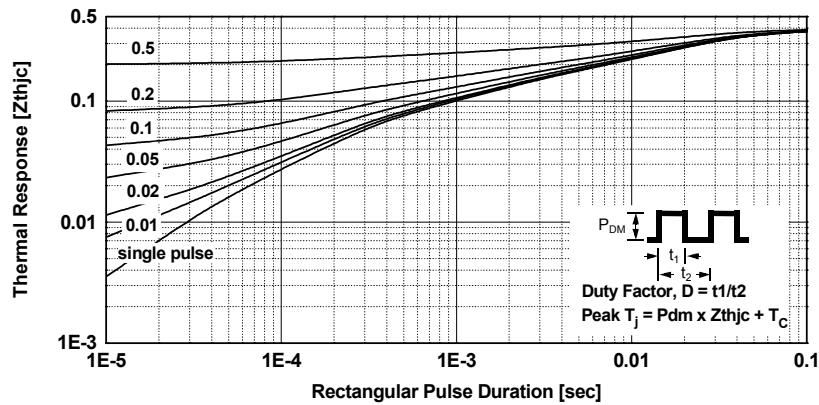
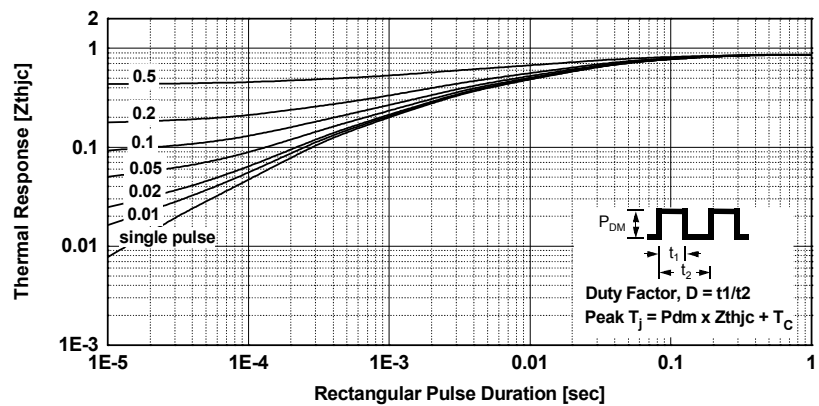
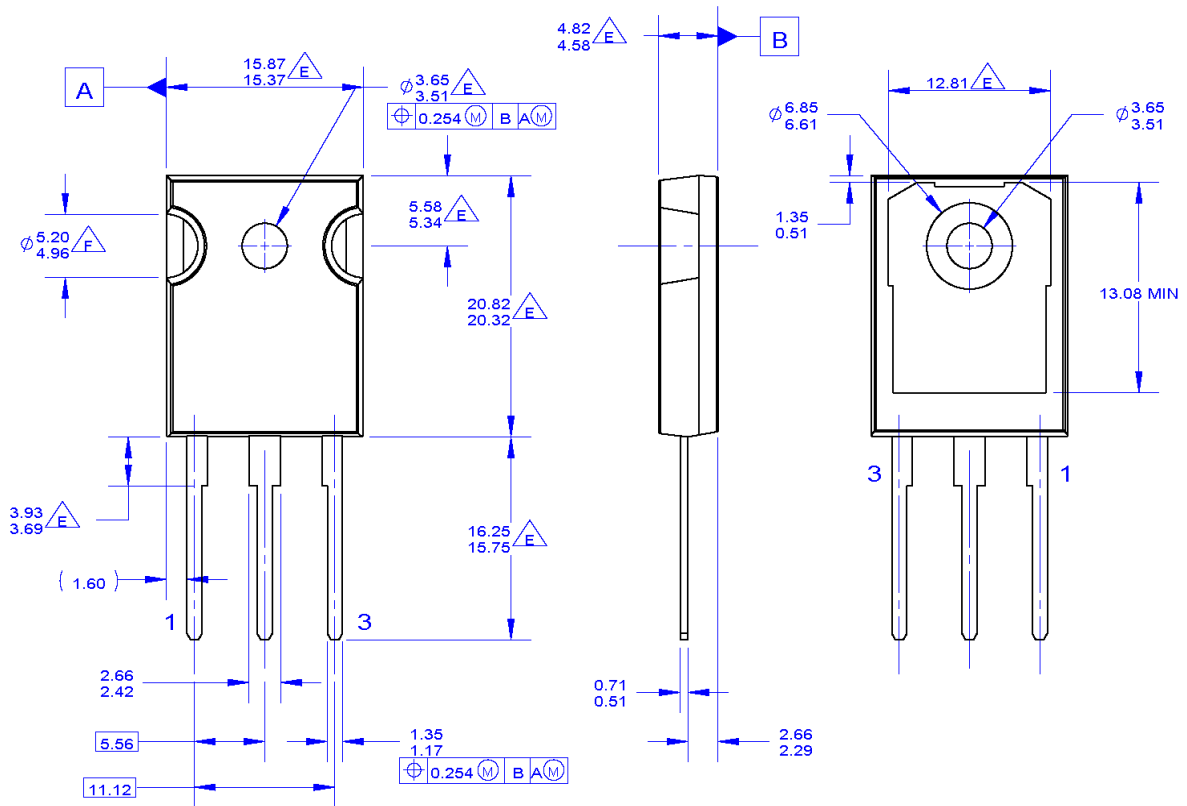


Figure 22. Transient Thermal Impedance of Diode



Mechanical Dimensions



NOTES: UNLESS OTHERWISE SPECIFIED.

- A. PACKAGE REFERENCE: JEDEC TO-247, ISSUE E, VARIATION AB, DATED JUNE, 2004.
- B. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.
- C. ALL DIMENSIONS ARE IN MILLIMETERS.
- D. DRAWING CONFORMS TO ASME Y14.5 - 1994

$\triangle E$ DOES NOT COMPLY JEDEC STANDARD VALUE

$\triangle F$ NOTCH MAY BE SQUARE

G. DRAWING FILENAME: MKT-TO247A03_REV03

Figure 23. TO-247, MOLDED, 3 LEAD, JEDEC VARIATION AB (Active)

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Dimensions in Millimeters

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